

JANHCB2N5679 & JANKCB2N5679

JANHCB2N5680 & JANKCB2N5680

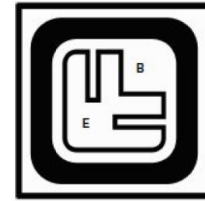


PNP Silicon Amplifier Chip

Rev. V1

Features

- JANHCB and JANKCB per MIL-PRF-19500/582
- Ideal for General Purpose Amplifier and Switching Applications Where High Voltages are Required



Electrical Characteristics ($T_A = +25^\circ\text{C}$ unless otherwise noted)

Parameter	Test Conditions	Symbol	Units	Min.	Max.
Collector - Emitter Breakdown Voltage	$I_C = -10 \text{ mA dc}$, 2N5679 $I_C = -10 \text{ mA dc}$, 2N5680	$V_{(BR)CEO}$	V dc	-100 -120	—
Collector - Emitter Cutoff Current	$V_{CE} = -70 \text{ V dc}$, 2N5679 $V_{CE} = -80 \text{ V dc}$, 2N5680	I_{CEO}	$\mu\text{A dc}$	—	-10 -10
Collector - Emitter Cutoff Current	$V_{CE} = -100 \text{ V dc}$, $V_{BE} = +1.5 \text{ Vdc}$, 2N5679 $V_{CE} = -120 \text{ V dc}$, $V_{BE} = +1.5 \text{ Vdc}$, 2N5680	I_{CEX1}	nA dc	—	-100 -100
Collector - Base Cutoff Current	$V_{CE} = -100 \text{ V dc}$, 2N5679 $V_{CE} = -120 \text{ V dc}$, 2N5680	I_{CBO}	nA dc	—	-100 -100
Emitter - Base Cutoff Current	$V_{BE} = -4.0 \text{ V dc}$	I_{EBO}	$\mu\text{A dc}$	—	-1.0
Forward Current Transfer Ratio	$I_C = -250 \text{ mA dc}$, $V_{CE} = -2.0 \text{ V dc}$ $I_C = -500 \text{ mA dc}$, $V_{CE} = -2.0 \text{ V dc}$ $I_C = -1.0 \text{ A dc}$, $V_{CE} = -2.0 \text{ V dc}$	h_{FE}	-	40 20 5	150
Collector - Emitter Saturation Voltage	$I_C = -250 \text{ mA dc}$, $I_B = -25 \text{ mA dc}$ $I_C = -500 \text{ mA dc}$, $I_B = -50 \text{ mA dc}$	$V_{CE(sat)1}$ $V_{CE(sat)2}$	V dc	—	-0.6 -1.0
Emitter - Base Saturation Voltage	$I_C = -250 \text{ mA dc}$, $I_B = -25 \text{ mA dc}$ $I_C = -500 \text{ mA dc}$, $I_B = -50 \text{ mA dc}$	$V_{BE(sat)1}$ $V_{BE(sat)2}$	V dc	—	-1.1 -1.3
Collector - Emitter Cutoff Current	$T_A = +150^\circ\text{C}$ $V_{CE} = -100 \text{ V dc}$, $V_{BE} = +1.5 \text{ Vdc}$, 2N5679 $V_{CE} = -120 \text{ V dc}$, $V_{BE} = +1.5 \text{ Vdc}$, 2N5680	I_{CEX2}	mA dc	—	-1.0 -1.0
Forward Current Transfer Ratio	$T_A = -55^\circ\text{C}$ $I_C = -250 \text{ mA dc}$, $V_{CE} = -2.0 \text{ V dc}$	h_{FE4}	-	20	
Dynamic Characteristics					
Magnitude of Small-Signal Short-Circuit Forward Current Transfer Ratio	$I_C = -0.1 \text{ A dc}$, $V_{CE} = -10 \text{ V dc}$, $f = 10 \text{ MHz}$	$ h_{FE} $	-	3	
Small-Signal Short-Circuit Forward Current Transfer Ratio	$I_C = -0.2 \text{ A dc}$, $V_{CE} = -1.5 \text{ V dc}$, $f = 1.0 \text{ kHz}$	h_{fe}	-	40	
Open Circuit Output Capacitance	$V_{CB} = -20 \text{ V dc}$, $I_E = 0$, $f = 1 \text{ MHz}$	C_{obo}	pF	—	50

JANHCB2N5679 & JANKCB2N5679

JANHCB2N5680 & JANKCB2N5680



PNP Silicon Amplifier Chip

Rev. V1

Absolute Maximum Ratings ($T_A = +25^\circ\text{C}$ unless otherwise noted)

Ratings	Symbol	Value
Collector - Emitter Voltage 2N5679 2N5680	V_{CEO}	-100 V dc -120 V dc
Collector - Base Voltage 2N5679 2N5680	V_{CBO}	-100 V dc -120 V dc
Emitter - Base Voltage	V_{EBO}	-4.0 V dc
Base Current	I_B	-0.5 A dc
Collector Current	I_C	-1.0 A dc
Operating & Storage Temperature Range	T_J, T_{STG}	-65°C to +200°C

Safe Operating Area

DC Tests:	$T_C = +25^\circ\text{C}$, 1 Cycle, $t \geq 0.5$ s
Test 1:	$I_C = -1.0$ A dc, $V_{CE} = -2$ V dc
Test 2:	$I_C = -1.0$ A dc, $V_{CE} = -10$ V dc
Test 3:	$I_C = -50$ mA dc, $V_{CE} = -90$ V dc

JANHCB2N5679 & JANKCB2N5679 JANHCB2N5680 & JANKCB2N5680



PNP Silicon Amplifier Chip

Rev. V1

Outline Drawing (Die)



B version

1. Chip size	.065 x .065 inch \pm .002 inch (1.651 X 1.651 \pm 0.0508 millimeter).
2. Chip thickness	.0134 inch \pm .0008 inch (0.34036 \pm 0.02032 millimeter).
3. Top metal	Aluminum, 54,000 Å minimum, 60,000 Å nominal.
4. Back metal	Al/Ti/Ni/Au 10,000 Å minimum, 12,000 Å nominal.
5. Backside	Collector.
6. Bonding pad	B = .017 inch x .017 inch (0.4318 X 0.4318 millimeter). E = .015 inch x .015 inch (0.381 X 0.381 millimeter).

* FIGURE 3 Physical dimensions for JANHCB and JANKCB die.

JANHCB2N5679 & JANKCB2N5679 JANHCB2N5680 & JANKCB2N5680



PNP Silicon Amplifier Chip

Rev. V1

VPT COMPONENTS. ALL RIGHTS RESERVED.

Information in this document is provided in connection with VPT Components products. These materials are provided by VPT Components as a service to its customers and may be used for informational purposes only. Except as provided in VPT Components Terms and Conditions of Sale for such products or in any separate agreement related to this document, VPT Components assumes no liability whatsoever. VPT Components assumes no responsibility for errors or omissions in these materials. VPT Components may make changes to specifications and product descriptions at any time, without notice. VPT Components makes no commitment to update the information and shall have no responsibility whatsoever for conflicts or incompatibilities arising from future changes to its specifications and product descriptions. No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document.

THESE MATERIALS ARE PROVIDED "AS IS" WITHOUT WARRANTY OF ANY KIND, EITHER EXPRESS OR IMPLIED, RELATING TO SALE AND/OR USE OF VPT COMPONENTS PRODUCTS INCLUDING LIABILITY OR WARRANTIES RELATING TO FITNESS FOR A PARTICULAR PURPOSE, CONSEQUENTIAL OR INCIDENTAL DAMAGES, MERCHANTABILITY, OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT. VPT COMPONENTS FURTHER DOES NOT WARRANT THE ACCURACY OR COMPLETENESS OF THE INFORMATION, TEXT, GRAPHICS OR OTHER ITEMS CONTAINED WITHIN THESE MATERIALS. VPT COMPONENTS SHALL NOT BE LIABLE FOR ANY SPECIAL, INDIRECT, INCIDENTAL, OR CONSEQUENTIAL DAMAGES, INCLUDING WITHOUT LIMITATION, LOST REVENUES OR LOST PROFITS, WHICH MAY RESULT FROM THE USE OF THESE MATERIALS.

VPT Components products are not intended for use in medical, lifesaving or life sustaining applications. VPT Components customers using or selling VPT Components products for use in such applications do so at their own risk and agree to fully indemnify VPT Components for any damages resulting from such improper use or sale.